

IN THE CLAIMS

This listing of claims replaces all prior listings.

1. (Previously Presented) A metal-oxide-compound semiconductor field effect transistor comprising:

 a nitride compound semiconductor wafer structure having an upper surface;
 a gate insulator structure comprising a first and second layer;
 said first layer substantially comprising compounds of gallium and oxygen
 said second layer comprising compounds of gallium and oxygen and at least one rare
 earth element;
 a gate electrode positioned on said gate insulator structure,
 source and drain regions self-aligned to said gate electrode; and
 source and drain ohmic contacts positioned on said source and drain areas;
 wherein gate electrode comprises a metal selected from the group refractory gate metals
 and combinations thereof;
 wherein the complete nitride MOS structure is built upon a a sapphire, silicon, SOI, AlN,
 or GaN substrate.

2.-70. Canceled.